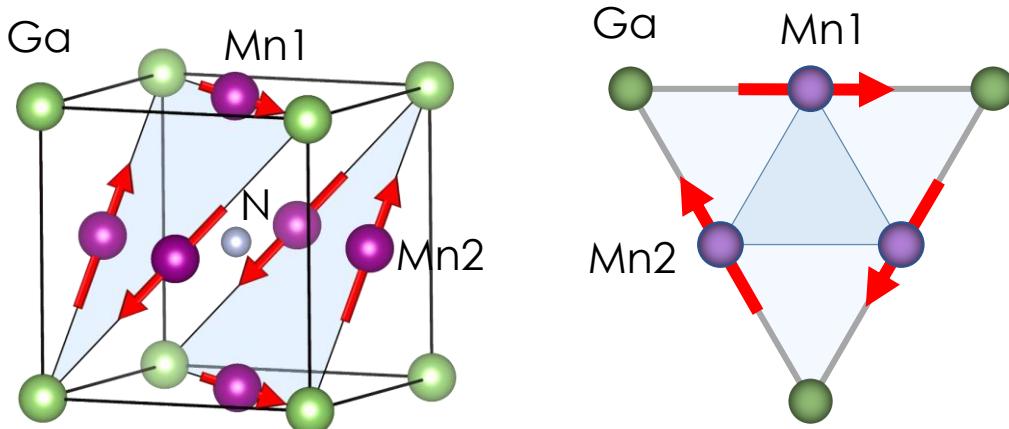


Modeling of  
the  $\text{Mn}_3\text{GaN}/\text{ABO}_3$  (001) Interface  
by density functional theory calculations

# Bulk Mn<sub>3</sub>GaN: Ground state



## Computational methods

- VASP+PAW+GGA
- E<sub>cutoff</sub>: 550 eV
- Kpoints: 16×16×16

Calculated Mn  
magnetic moments ( $\mu_B$ )

	a (Å)	m ( $\mu_B$ /Mn)
This work	3.866	2.438
Experiment	3.886 [1]	2.68(5) [1]
Previous theory	3.86 [2,3]	2.4 [2], 2.43 [3]

	m <sub>x</sub>	m <sub>y</sub>	m <sub>z</sub>	m <sub>Tot</sub>
Mn1	1.724	1.724	0	2.438
Mn2	-1.724	0	1.724	2.438
	0	-1.724	-1.724	2.438

[1] K. Shi et al., Adv. Mater. 28, 3761 (2016)

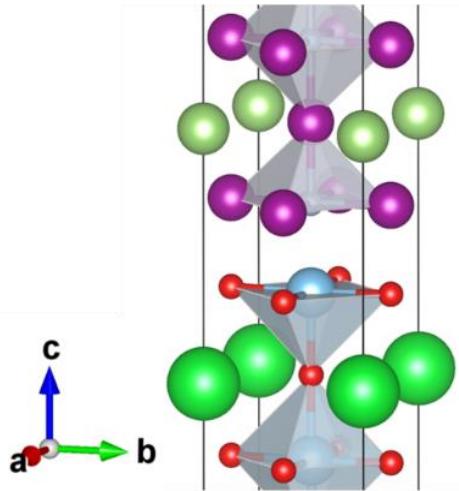
[2] P. Lukashev et al., PRB 78, 184414 (2008)

[3] J. Zemen et al., arXiv:1512.03470 (2015)

Ground state of bulk GaN<sub>Mn</sub><sub>3</sub> successfully reproduced

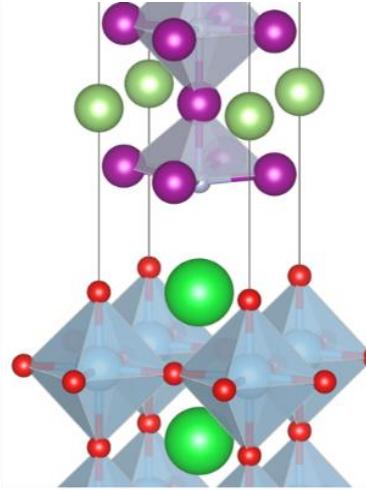
# Mn<sub>3</sub>GaN/SrTiO<sub>3</sub>: Interface stability

4GaNMn<sub>3</sub>·NMn<sub>2</sub>/4SrTiO<sub>3</sub>·TiO<sub>2</sub>



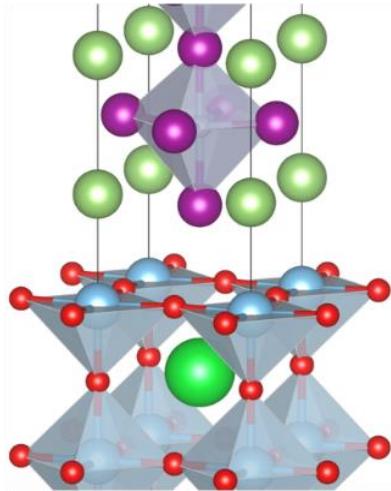
NMn<sub>2</sub>/TiO<sub>2</sub>

4GaNMn<sub>3</sub>·NMn<sub>2</sub>/4SrTiO<sub>3</sub>·SrO



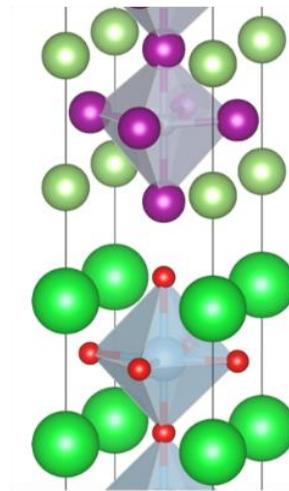
NMn<sub>2</sub>/SrO

4GaNMn<sub>3</sub>·GaMn/4SrTiO<sub>3</sub>·TiO<sub>2</sub>



GaMn/TiO<sub>2</sub>

4GaNMn<sub>3</sub>·GaMn/4SrTiO<sub>3</sub>·SrO



GaMn/SrO

- VASP+PAW+GGA
- E<sub>cutoff</sub>: 550 eV
- Kpoints: 16×16×1
- a<sub>inplane</sub>=a<sub>SrTiO<sub>3</sub></sub>=3.945 Å
- Γ<sub>5g</sub> non-collinear magnetism

$$\Delta E_{Mn_2N\_TiO_2} = (E_{supercell} - 4E_{Mn_3GaN} - 4E_{SrTiO_3} - E_{Ti} - 2E_O - E_N - 2E_{Mn})/2,$$

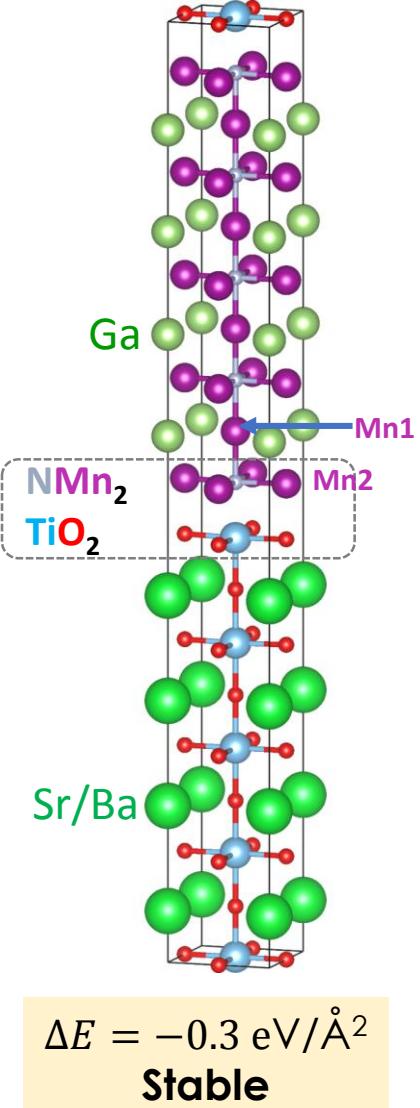
$$\Delta E_{Mn_2N\_SrO} = (E_{supercell} - 4E_{Mn_3GaN} - 4E_{SrTiO_3} - E_{Sr} - E_O - E_N - 2E_{Mn})/2,$$

$$\Delta E_{GaMn\_TiO_2} = (E_{supercell} - 4E_{Mn_3GaN} - 4E_{SrTiO_3} - E_{Ti} - 2E_O - E_{Ga} - E_{Mn})/2,$$

$$\Delta E_{GaMn\_SrO} = (E_{supercell} - 4E_{Mn_3GaN} - 4E_{SrTiO_3} - E_{Sr} - E_O - E_{Ga} - E_{Mn})/2$$

Interface structure	NMn <sub>2</sub> /TiO <sub>2</sub>	NMn <sub>2</sub> /SrO	GaMn/TiO <sub>2</sub>	GaMn/SrO
ΔE (eV/interface)	-4.785	-2.295	-2.965	-2.187

# Mn<sub>3</sub>GaN/ATiO<sub>3</sub> (A=Sr,Ba): Interface structure



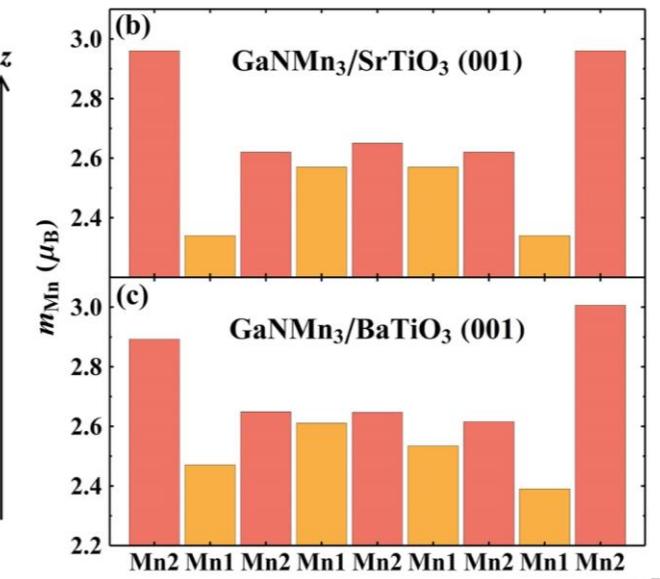
Interfacial Mn2-O and Mn2-Ti distances along the  $z$  direction for GaNMn<sub>3</sub>/ATiO<sub>3</sub> (A=Sr, Ba).  $P=0$  corresponds to GaNMn<sub>3</sub>/SrTiO<sub>3</sub>, while  $P>0$  and  $P<0$  correspond to GaNMn<sub>3</sub>/BaTiO<sub>3</sub> with polarization pointing toward to and away from the interface, respectively.

	Mn2-O z-distance (Å)	Mn2-Ti z-distance (Å)	Ti-N z-distance (Å)
GaNMn <sub>3</sub> /SrTiO <sub>3</sub> ( $P = 0$ )	2.087	2.138	2.096
GaNMn <sub>3</sub> /BaTiO <sub>3</sub> ( $P > 0$ )	2.074	1.983	2.015
GaNMn <sub>3</sub> /BaTiO <sub>3</sub> ( $P < 0$ )	2.065	2.253	2.173

# $\text{Mn}_3\text{GaN}/\text{ATiO}_3$ (A=Sr,Ba): Magnetsim

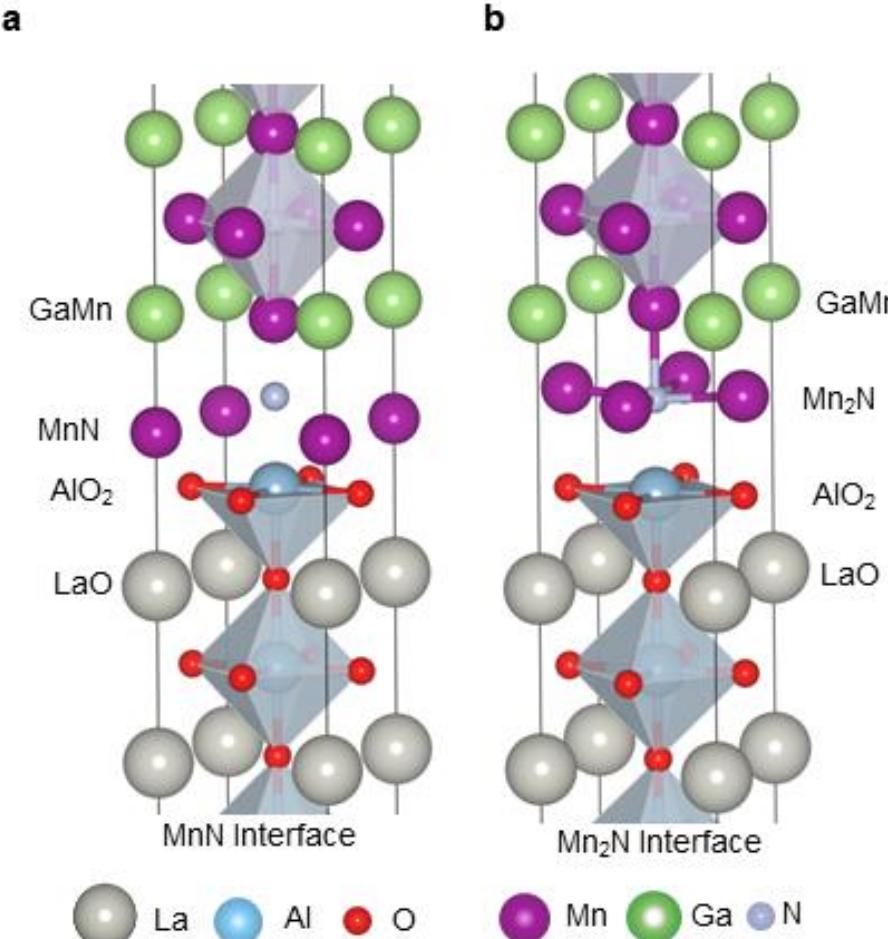
The calculated magnetic moments ( $\mu_{\text{B}}$ ) of Mn atoms in  $\text{GaNMn}_3/\text{ATiO}_3$  (A=Sr, Ba).

	$\text{GaNMn}_3/\text{SrTiO}_3$				$\text{GaNMn}_3/\text{BaTiO}_3$			
	$m_x$	$m_y$	$m_z$	$m_{total}$	$m_x$	$m_y$	$m_z$	$m_{total}$
Mn2	0.299	-1.927	-2.227	2.960	-0.732	1.575	2.306	2.887
	-1.929	0.298	2.225	2.960	1.576	-0.732	-2.306	2.887
Mn1	1.659	1.658	0.001	2.345	-1.746	-1.744	0.002	2.468
Mn2	0.183	-1.753	-1.936	2.618	-0.153	1.788	1.940	2.643
	-1.754	0.182	1.935	2.618	1.786	-0.157	-1.942	2.643
Mn1	1.814	1.814	0.001	2.565	-1.839	-1.837	0.002	2.599
Mn2	0.033	-1.854	-1.887	2.646	-0.063	1.832	1.894	2.636
	-1.854	0.033	1.887	2.646	1.830	-0.066	-1.896	2.636
Mn1	1.814	1.814	0.000	2.565	-1.785	-1.784	0.001	2.524
Mn2	0.183	-1.754	-1.936	2.619	-0.181	1.748	1.929	2.609
	-1.753	0.182	1.936	2.618	1.747	-0.184	-1.930	2.610
Mn1	1.659	1.659	0.000	2.346	-1.684	-1.684	0.001	2.382
Mn2	0.300	-1.927	-2.226	2.959	-0.026	2.112	2.137	3.005
	-1.926	0.301	2.227	2.960	2.111	-0.028	-2.138	3.005



# Mn<sub>3</sub>GaN/LaAlO<sub>3</sub>: Interface stability

4GaN Mn<sub>3</sub>·NMn/4SrTiO<sub>3</sub>·TiO<sub>2</sub>    4GaN Mn<sub>3</sub>·NMn<sub>2</sub>/4SrTiO<sub>3</sub>·SrO

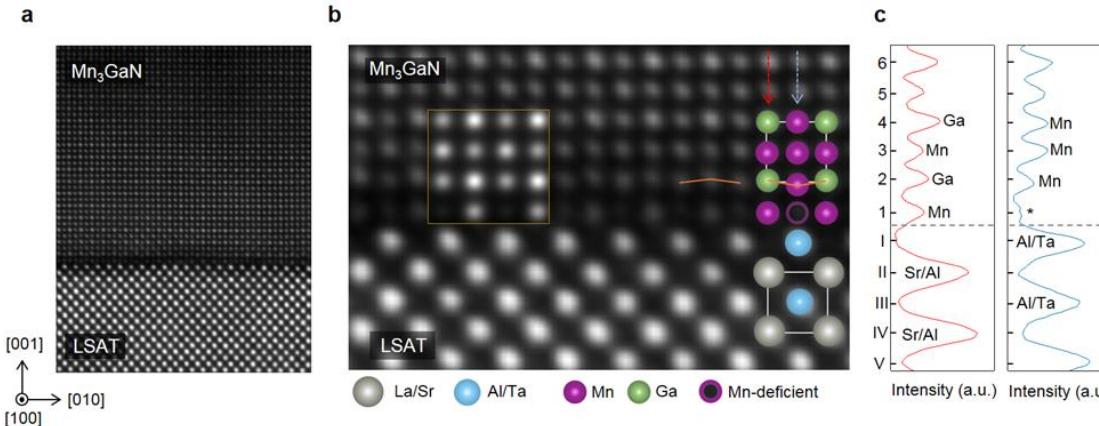


- VASP+PAW+GGA
- E<sub>cutoff</sub>: 550 eV
- Kpoints: 16×16×1
- a<sub>inplane</sub>=a<sub>Mn<sub>3</sub>GaN</sub>=3.867 Å
- Γ<sub>5g</sub> non-collinear magnetism

$$\Delta E_{MnN\_interface} = (E_{supercell} - 4E_{Mn_3GaN} - 4E_{LaAlO_3} - E_{Al} - E_N - 2E_O)/2,$$
$$\Delta E_{Mn_2N\_interface} = (E_{supercell} - 4E_{Mn_3GaN} - 4E_{LaAlO_3} - E_{Al} - E_N - 2E_O - 2E_{Mn})/2$$

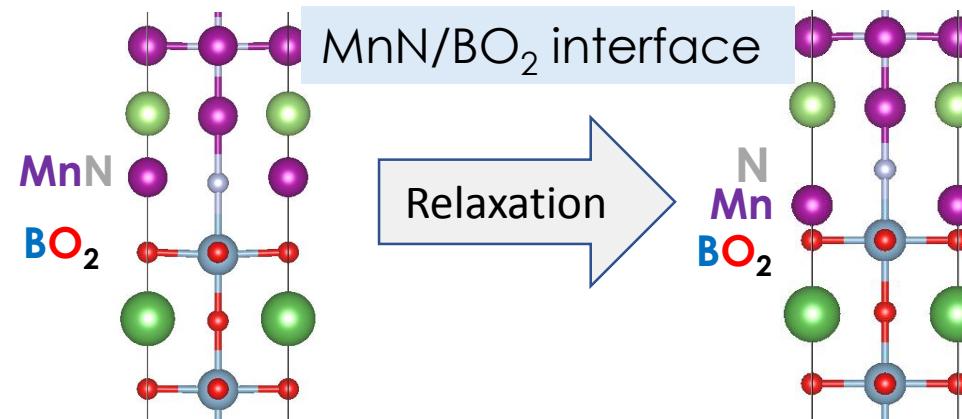
	Mn <sub>3</sub> GaN/LaAlO <sub>3</sub> (MnN interface)	Mn <sub>3</sub> GaN/LaAlO <sub>3</sub> (Mn <sub>2</sub> N interface)
ΔE (eV/interface)	-0.058	-2.265

# $Mn_3GaN$ : Tests of different interfacial configuration



## Experiment:

- MnN interfacial monolayer
- GaMn puckered layer

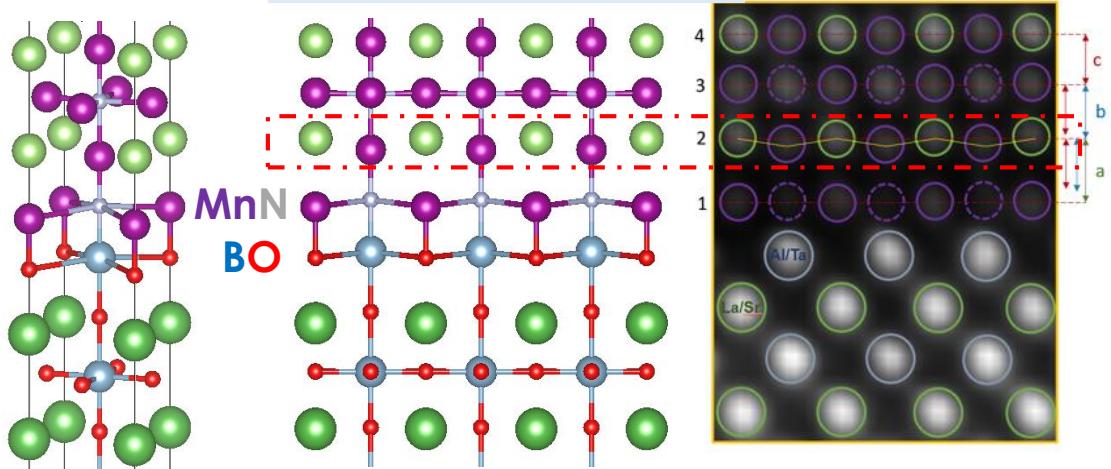


Non-magnetic MnN/BO<sub>2</sub> interface doesn't have puckered GaMn layer

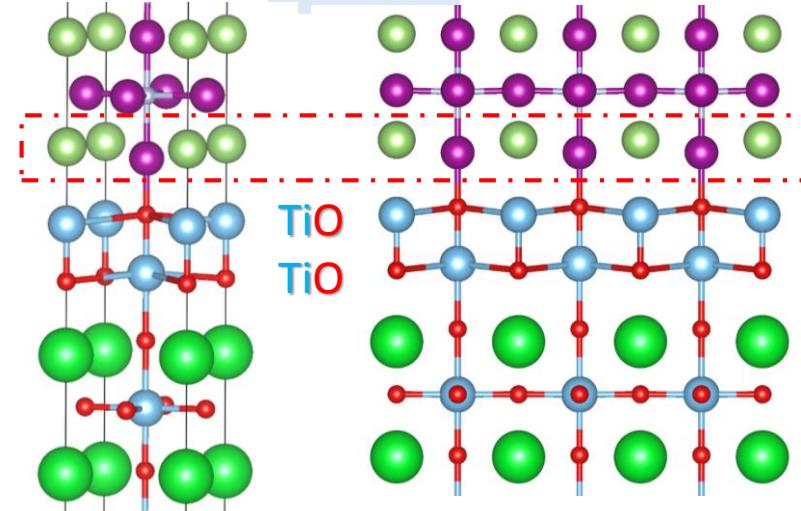
- VASP+PAW+GGA
- E<sub>cutoff</sub>: 550 eV
- Kpoints: 16×16×1
- Non-magnetism

# $Mn_3GaN$ : Tests of different interfacial configuration

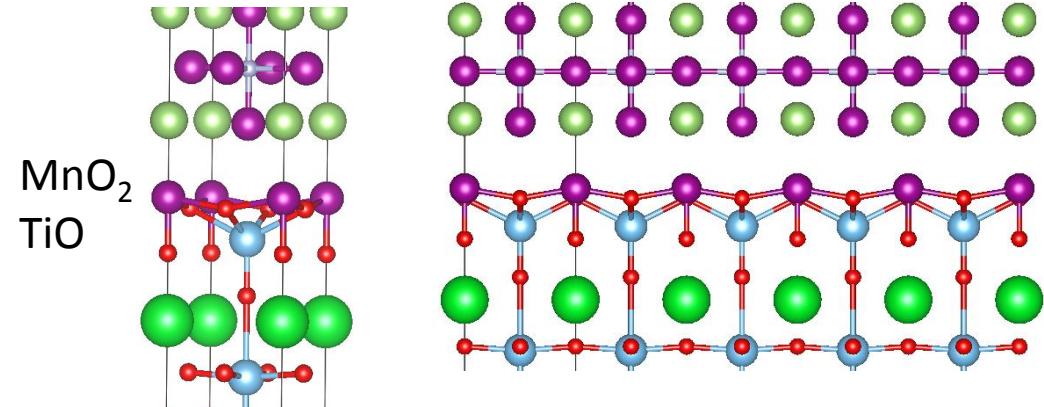
MnN/BO interface



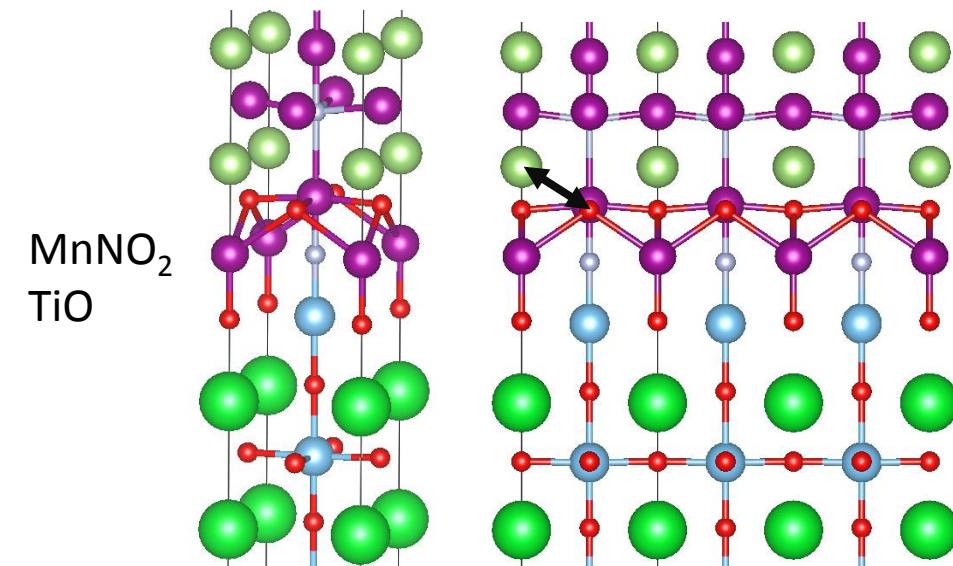
TiO/TiO



$MnO_2/TiO$  interface

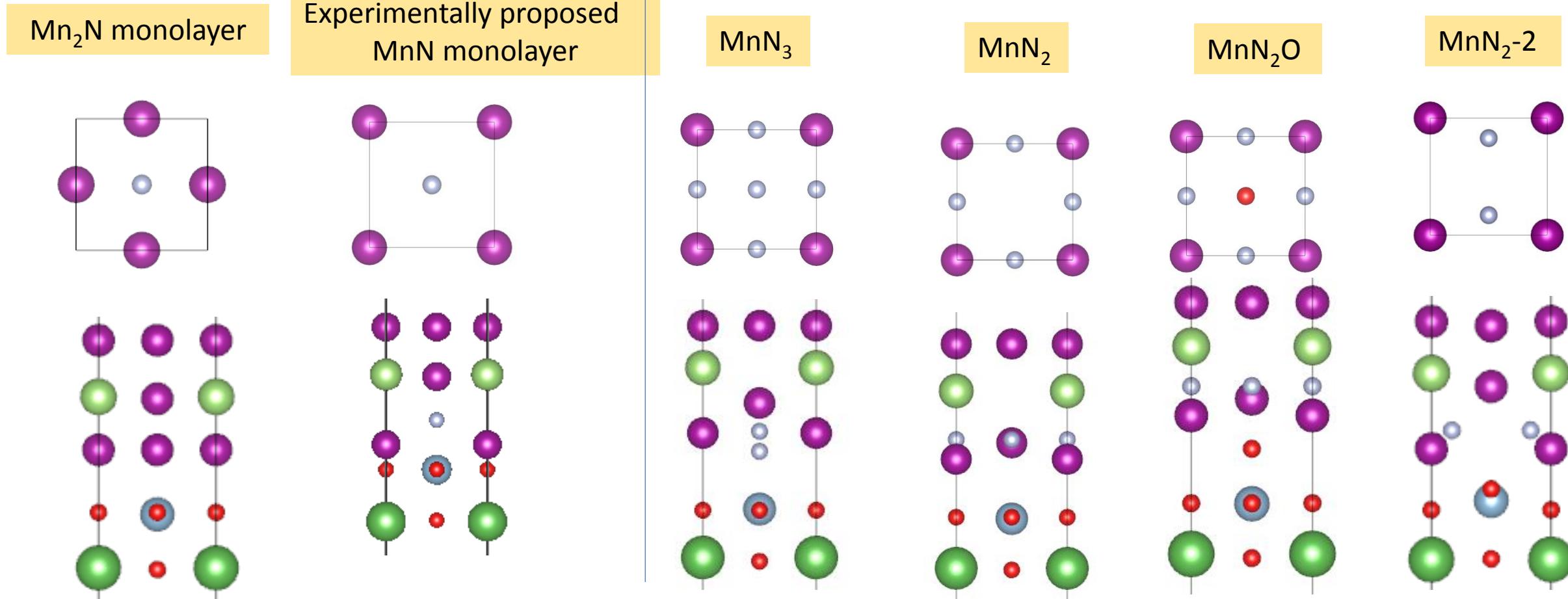


$MnNO_2/TiO$



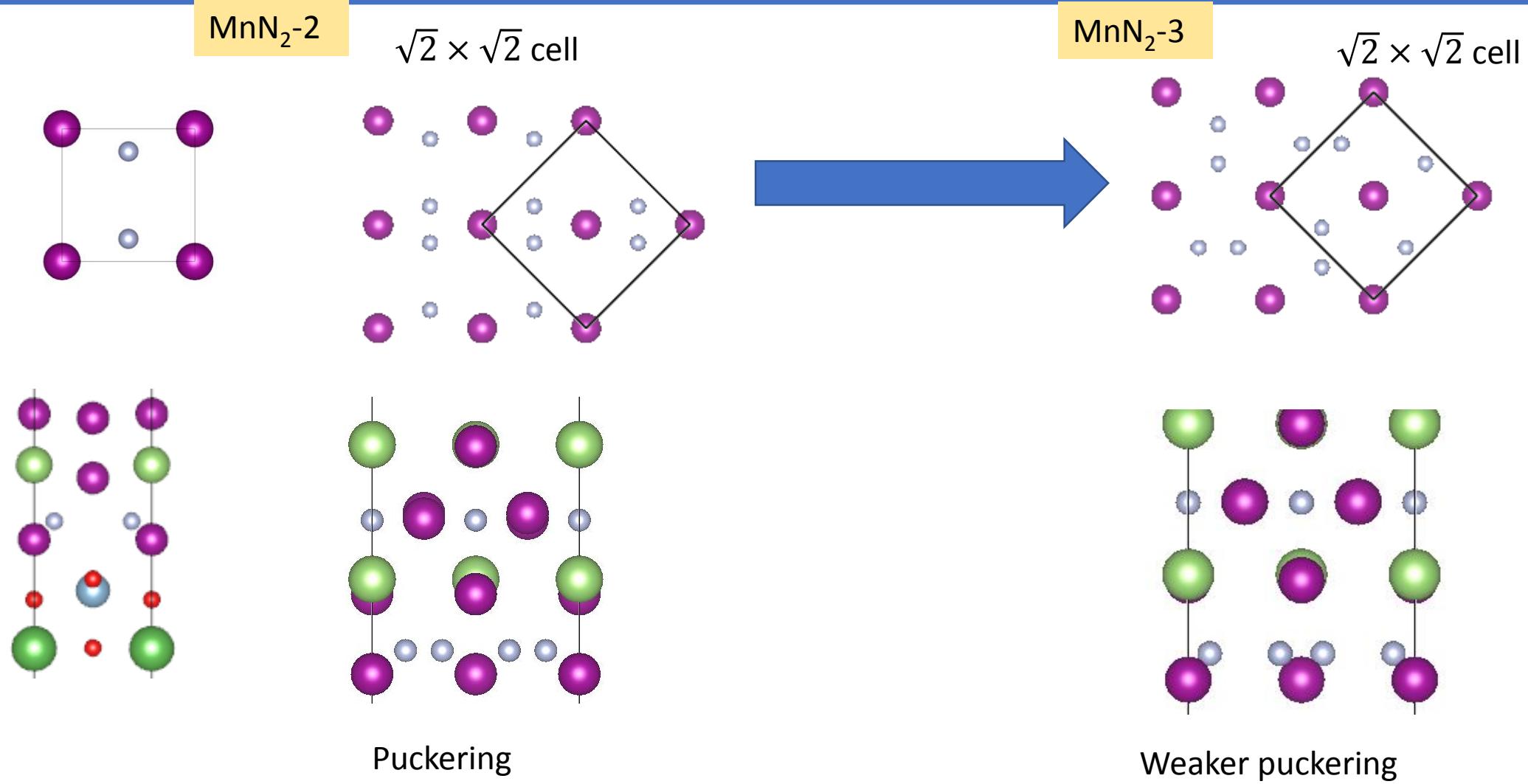
# $\text{Mn}_3\text{GaN}/\text{LaAlO}_3$ : N rich interfaces

Fix  $a=3.764 \text{ \AA}$  ( $a_{\text{GGA}}$  of non magnetic bulk  $\text{GaNMn}_3$ ), relax  $c$  without magnetism



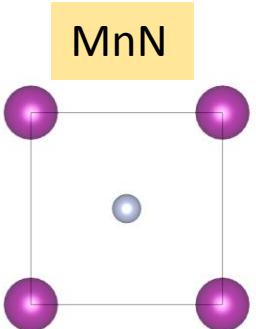
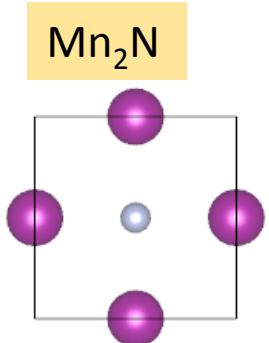
- $\text{MnN}_2\text{-}2$  seems to be a reasonable model to reproduce the puckering

# $\text{Mn}_3\text{GaN}/\text{LaAlO}_3$ : N rich interfaces

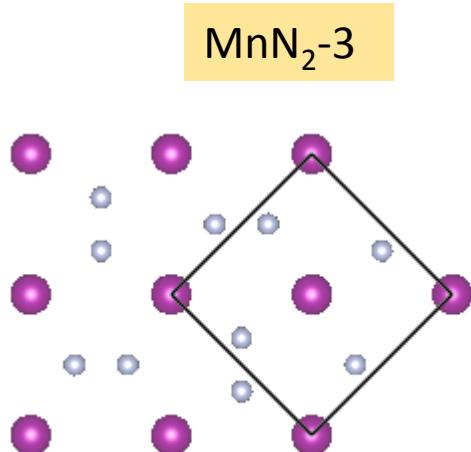
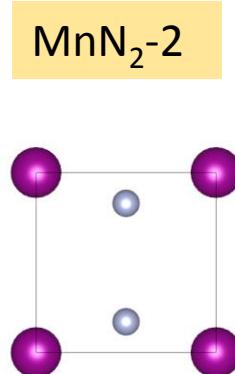


- **MnN<sub>2</sub>-3 show weaker puckering structure**

# $Mn_3GaN/LaAlO_3$ : N rich interfaces



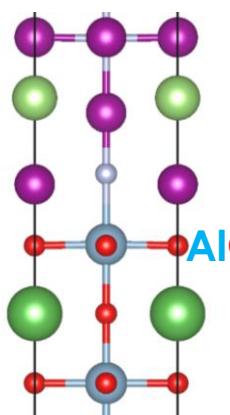
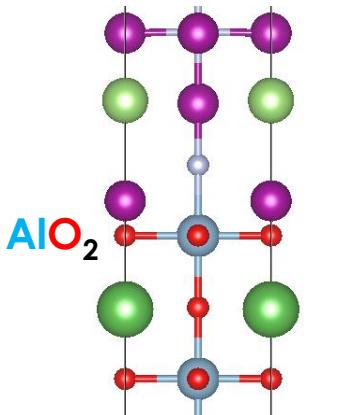
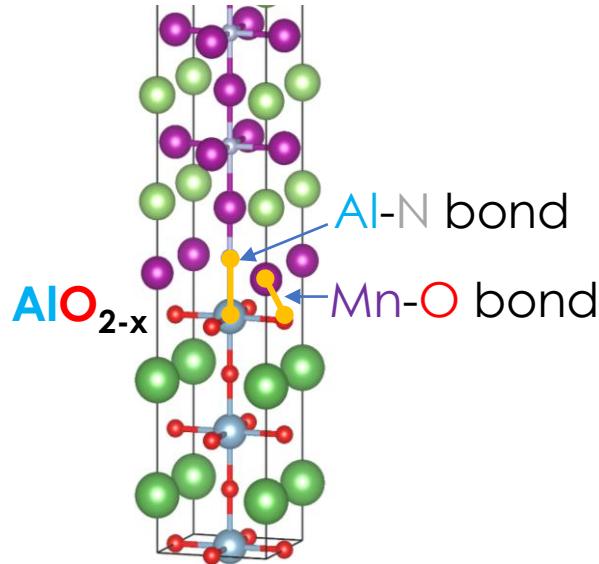
- VASP+PAW+GGA
- $E_{\text{cutoff}}$ : 550 eV
- Kpoints:  $16 \times 16 \times 1$
- Non-magnetism
- VCA for O deficiency



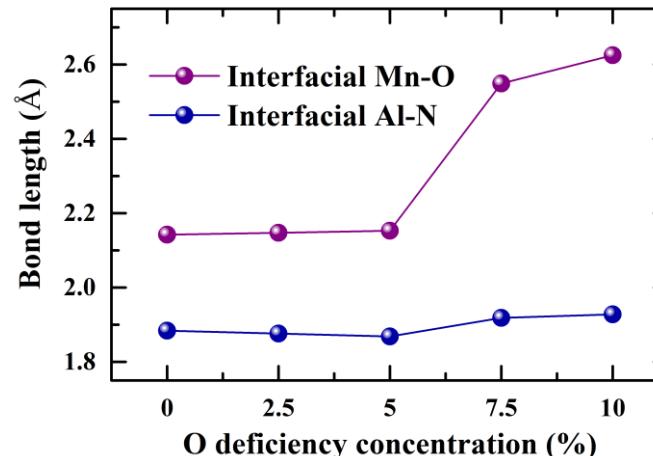
	Formation energy (eV/interface)
Mn2N-supercell ( $Mn_2N/AlO_2$ )	-5.676
MnN-supercell ( $MnN/AlO_2$ )	-1.459
MnN <sub>2</sub> -2-supercell	-1.638
MnN <sub>2</sub> -3-supercell /2	-1.205

$Mn_2N$  structure is more energy favorable

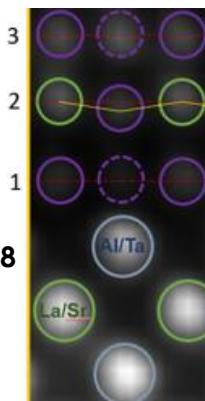
# $\text{Mn}_3\text{GaN}/\text{LaAlO}_3$ : O deficiency



O deficiency simulated by virtual crystal approximation (VCA)



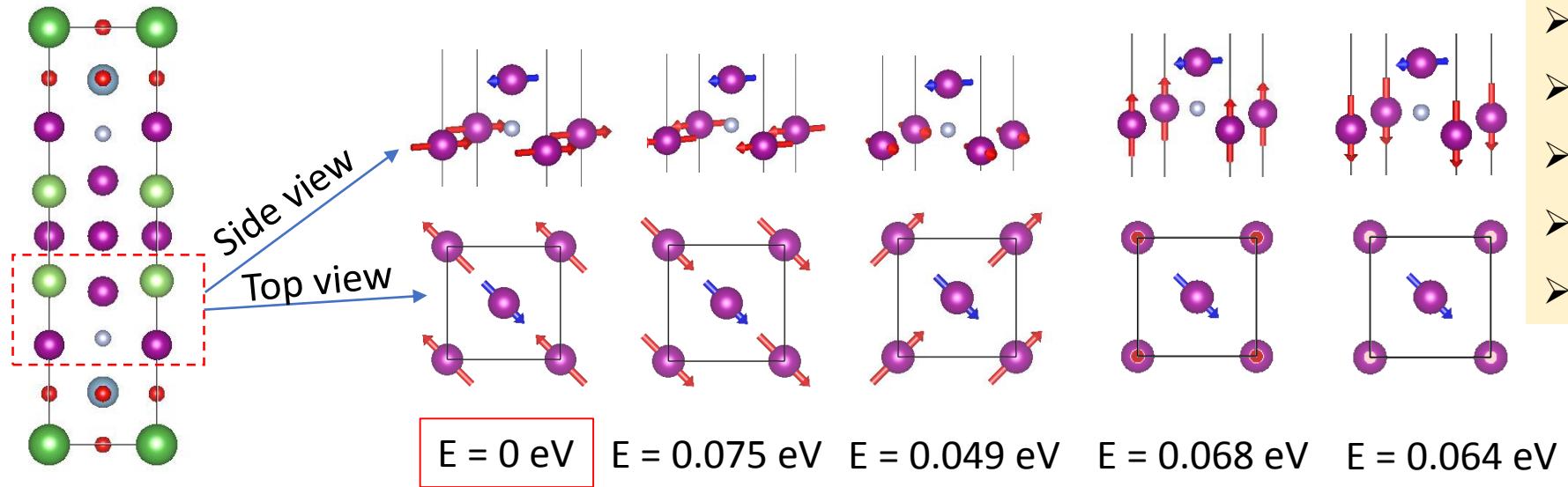
- VASP+PAW+GGA
- $E_{\text{cutoff}}$ : 550 eV
- Kpoints:  $16 \times 16 \times 1$
- Non-magnetism
- VCA for O deficiency



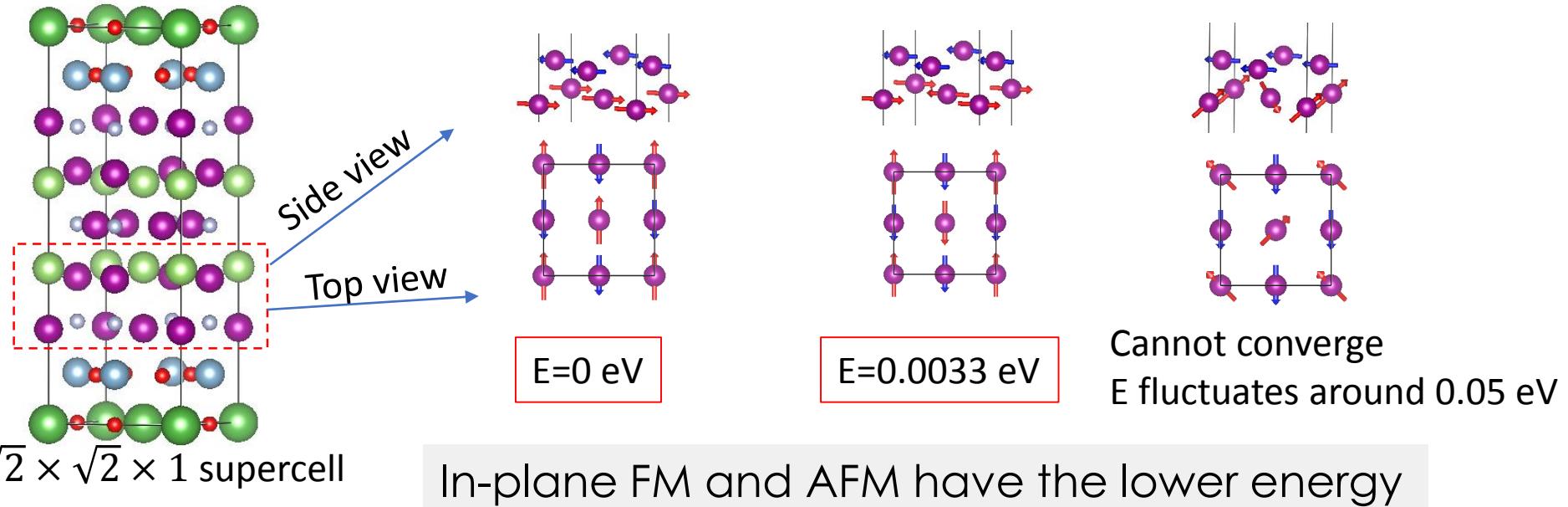
	Mn-O bond length (Å)	Al-N bond length (Å)
$\text{MnN}/\text{AlO}_2$	2.142	1.884
$\text{MnN}/\text{AlO}_{1.95}$	2.147	1.876
$\text{MnN}/\text{AlO}_{1.9}$	2.153	1.869
$\text{MnN}/\text{AlO}_{1.85}$	2.549	1.919
$\text{MnN}/\text{AlO}_{1.8}$	2.625	1.928

- Interfacial structure reproduced with  $\text{MnN}/\text{AlO}_{2-x}$  configuration

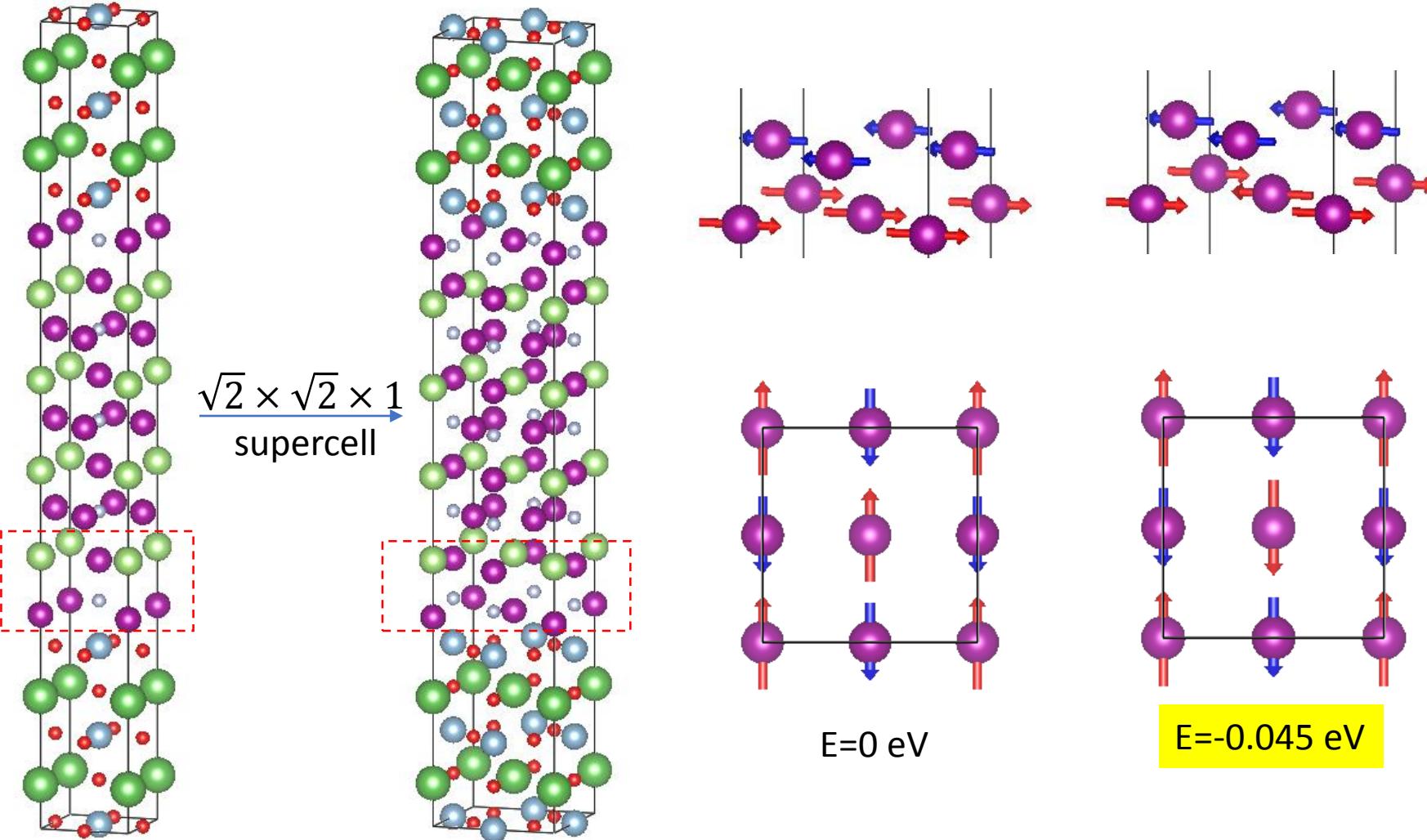
# $\text{Mn}_3\text{GaN}/\text{LaAlO}_3$ : Magnetsim in small cell



- VASP+PAW+GGA
- $E_{\text{cutoff}}: 550 \text{ eV}$
- Kpoints:  $16 \times 16 \times 1$
- $a_{\text{inplane}} = a_{\text{Mn}_3\text{GaN}} = 3.867 \text{ \AA}$
- $\Gamma_{5g}$  non-collinear magnetism



# Mn<sub>3</sub>GaN/LaAlO<sub>3</sub>: Magnetsim in large cell



The magnetism at interfacial layer should be AFM